NSN 5961-00-434-3201

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No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-00-434-3201 **Inclosure Material:** Metal **Overall Length:** Between 0.470 inches and 0.500 inches Overall Diameter: 0.620 inches **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 160.0 breakdown voltage, collector-to-base, emitter open and 140.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open and 150.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter **Current Rating Per Characteristic:** Between 2.00 amperes source cutoff current and 3.00 amperes source cutoff current **Power Rating Per Characteristic:** 25.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:**